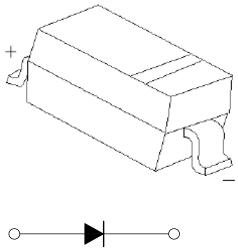
JCST

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-123 Plastic-Encapsulate Diodes

SOD-123



MMSD914 SMALL SIGNAL DIODE

FEATURES

- High Voltage

MARKING: 5D

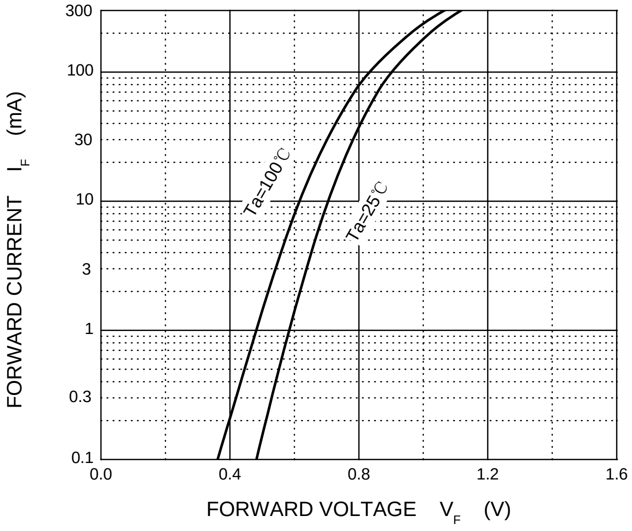
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage	100	V
I_O	Forward Current	0.2	A
I_{FSM}	Non-repetitive Peak Forward Surge Current @t=1ms	2	
P_D	Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	312	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

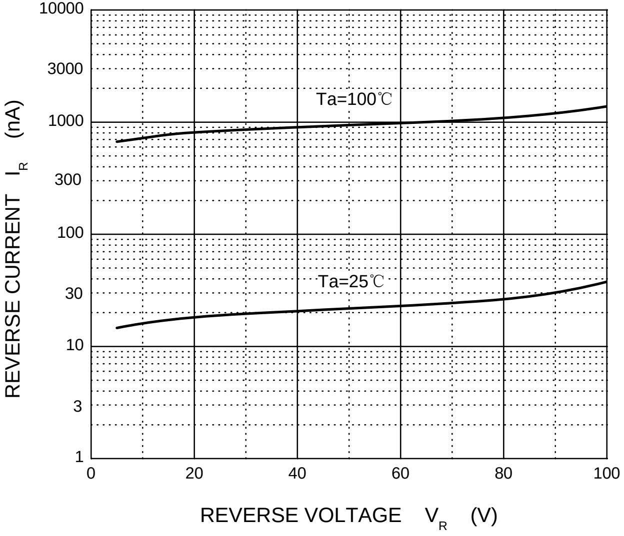
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=5μA	75			V
		I_R=100μA	100			V
Reverse current	I_R	V_R=20V			25	nA
		V_R=75V			5	μA
Forward voltage	V_F	I_F=10mA			1	V
Total capacitance	C_{tot}	V_R=0V,f=1MHz			4	pF
Reverse recovery time	t_{rr}	I_F= I_R=30mA, I_{rr}=0.1×I_R, R_L=100Ω			4	ns

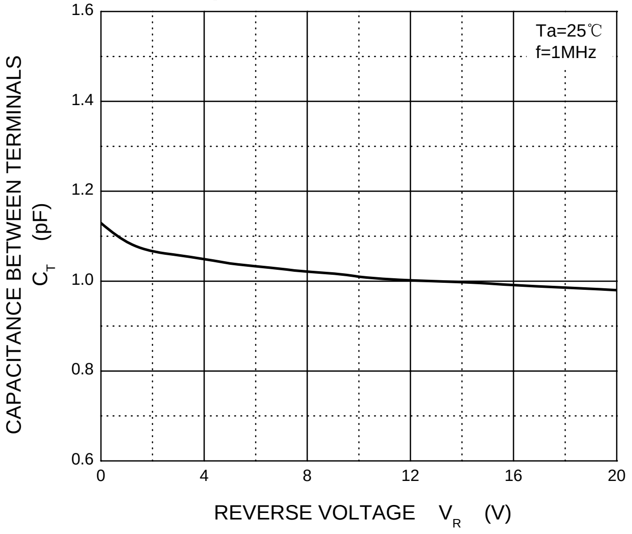
Typical Characteristics MMSD914



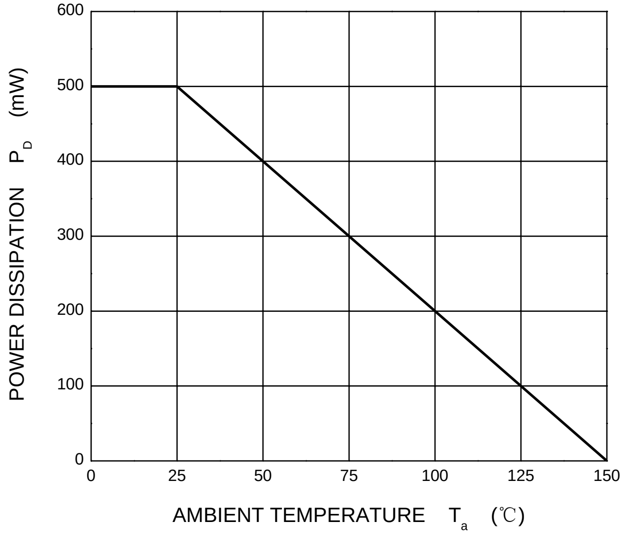
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve